

METHOD OF PREPARING THE SURFACE OF A SEMICONDUCTOR
WAFER TO MAKE IT EPIREADY

ABSTRACT

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The invention concerns a method of preparing the surface of a semiconductor wafer intended for microelectronics and/or optoelectronics applications. In particular, a method of preparing a SiC surface of a semiconductor wafer to make it epiready is described. The technique includes annealing the wafer in an oxidizing 10 atmosphere, and polishing a surface of the wafer with an abrasive based on particles of colloidal silica to make the SiC wafer surface suitable for homoepitaxy or heteroepitaxy.

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